

### Features

- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

### Description

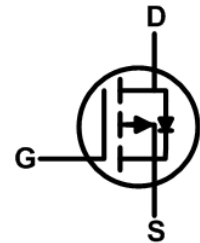
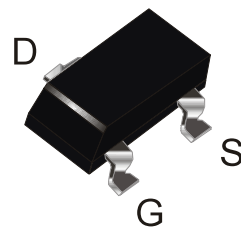
The JHT3107 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The JHT3107 meet the RoHS and Green Product requirement with full function reliability approved.

### Product Summary

BVDSS	RDSON	ID
-30V	70mΩ	-3.2A

### SOT-23 S Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		10s	Steady State	
V <sub>DS</sub>	Drain-Source Voltage	-30		V
V <sub>GS</sub>	Gate-Source Voltage	±20		V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-3.6	-3.2	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup>	-2.9	-2.5	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-13		A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>3</sup>	1.32	1	W
P <sub>D</sub> @T <sub>A</sub> =70°C	Total Power Dissipation <sup>3</sup>	0.84	0.64	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150		°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150		°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sup>1</sup>	---	125	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤ 10s)	---	95	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	80	°C/W

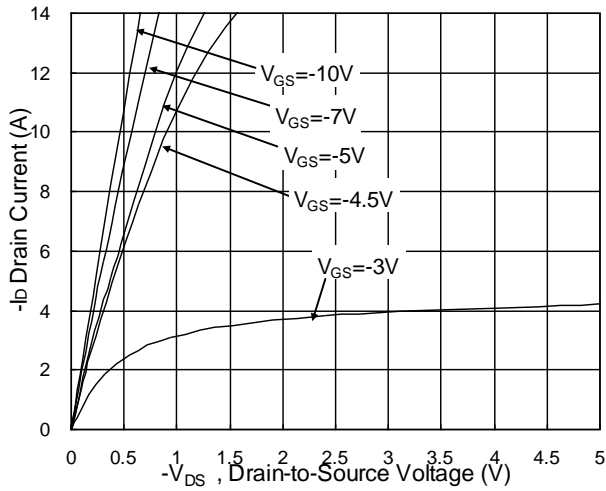
## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.]	Typ.	Max.]	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA	---	-0.02	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-3A	---	55	70	mΩ
		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1.5A	---	90	120	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.2	-1.5	-2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.32	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	-5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-3A	---	4.8	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	---	24	48	Ω
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-20V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-3A	---	5.22	7.3	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.25	1.8	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.3	3.2	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V , V <sub>GS</sub> =-10V , R <sub>G</sub> =3.3Ω I <sub>D</sub> =-1A	---	18.4	37	ns
T <sub>r</sub>	Rise Time		---	11.4	21	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	39.4	79	
T <sub>f</sub>	Fall Time		---	5.2	10.4	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , f=1MHz	---	463	650	pF
C <sub>oss</sub>	Output Capacitance		---	82	115	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	68	95	
<b>Diode Characteristics</b>						
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	-3.2	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	-13	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C	---	---	-1	V

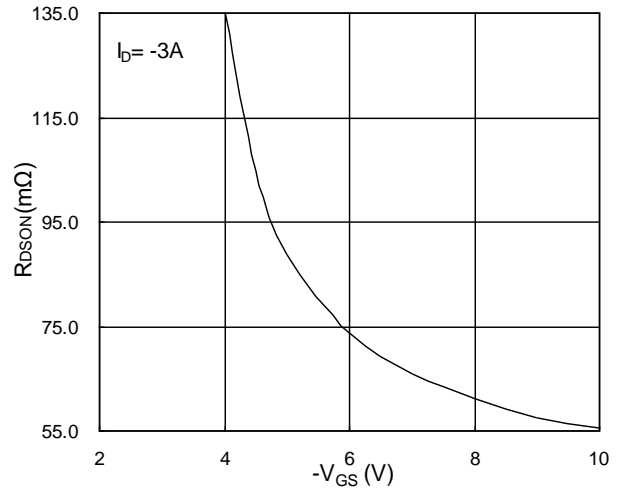
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

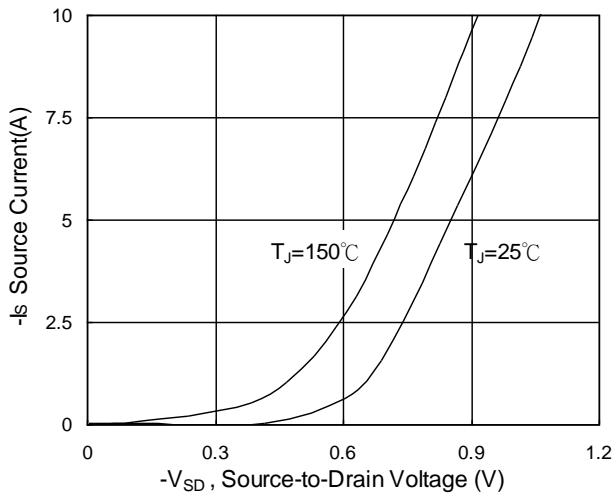
## Typical Characteristics



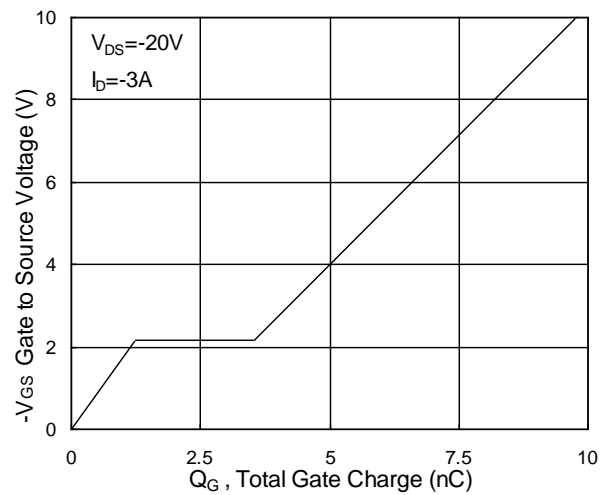
**Fig.1 Typical Output Characteristics**



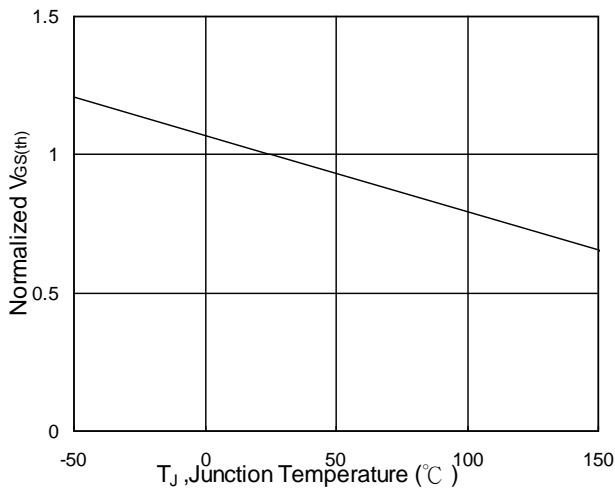
**Fig.2 On-Resistance vs. G-S Voltage**



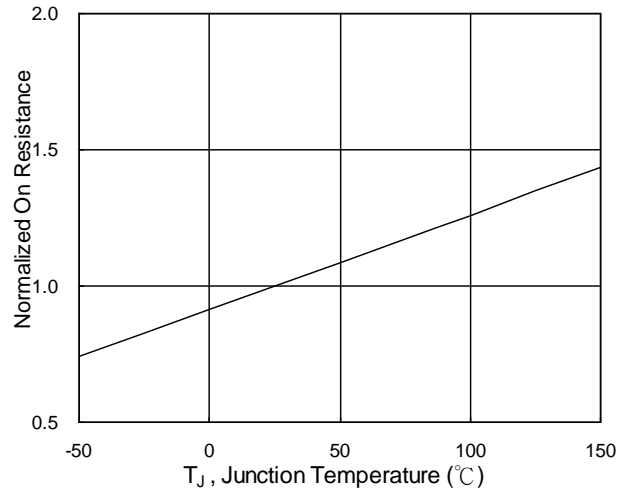
**Fig.3 Source Drain Forward Characteristics**



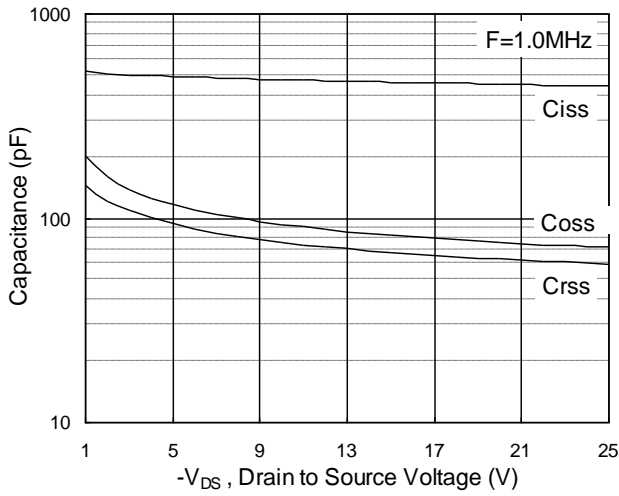
**Fig.4 Gate-Charge Characteristics**



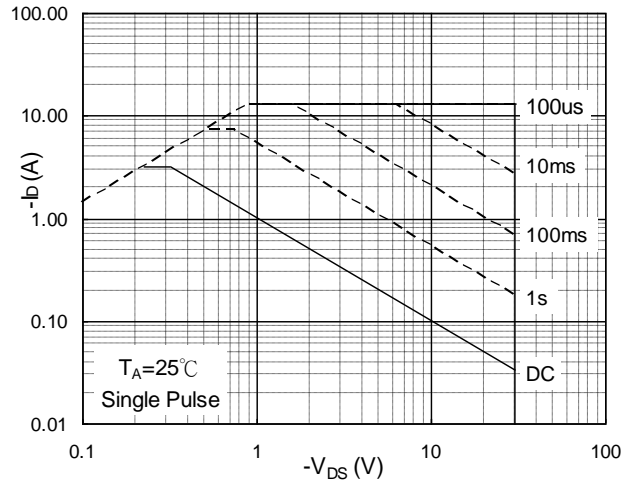
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



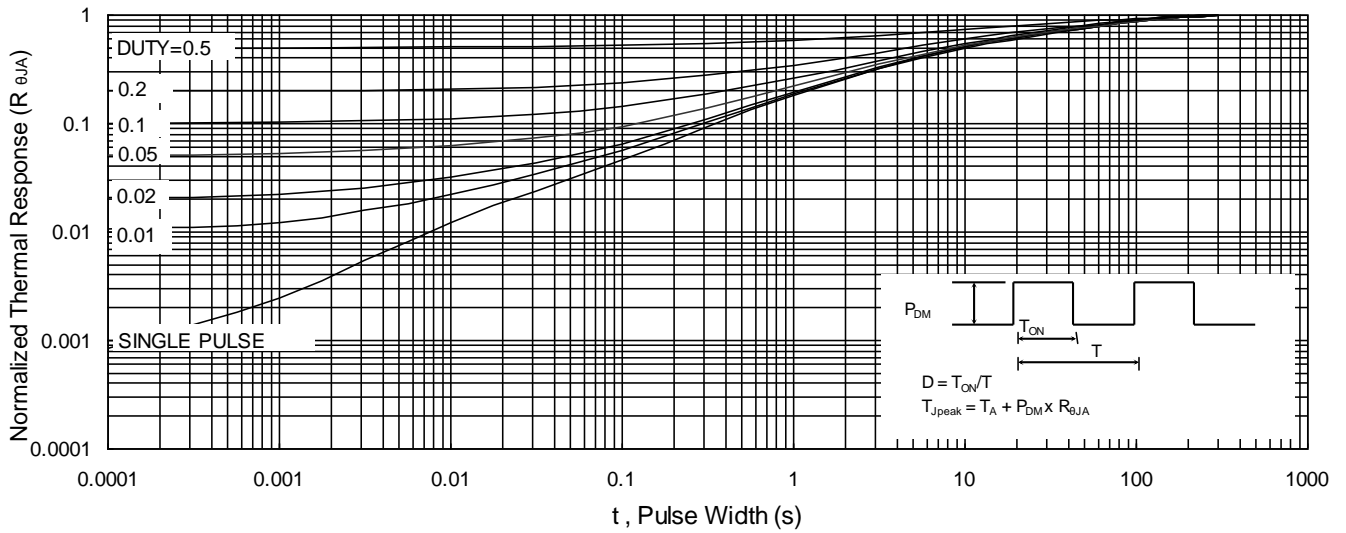
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



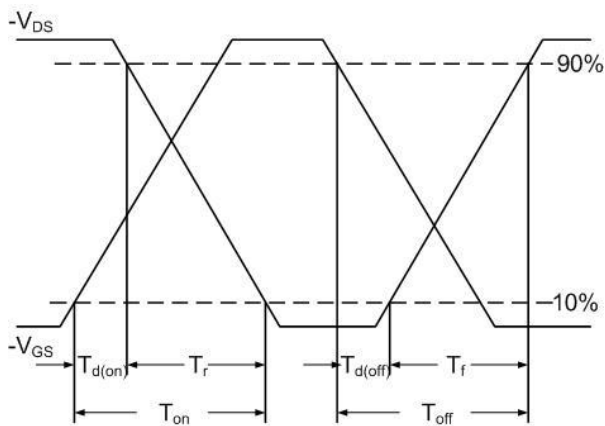
**Fig.7 Capacitance**



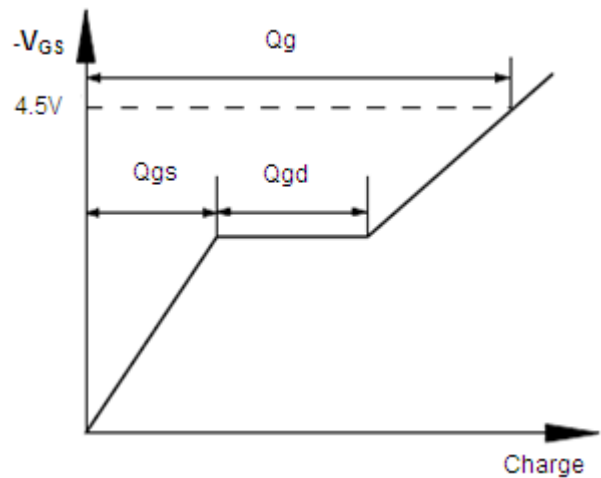
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



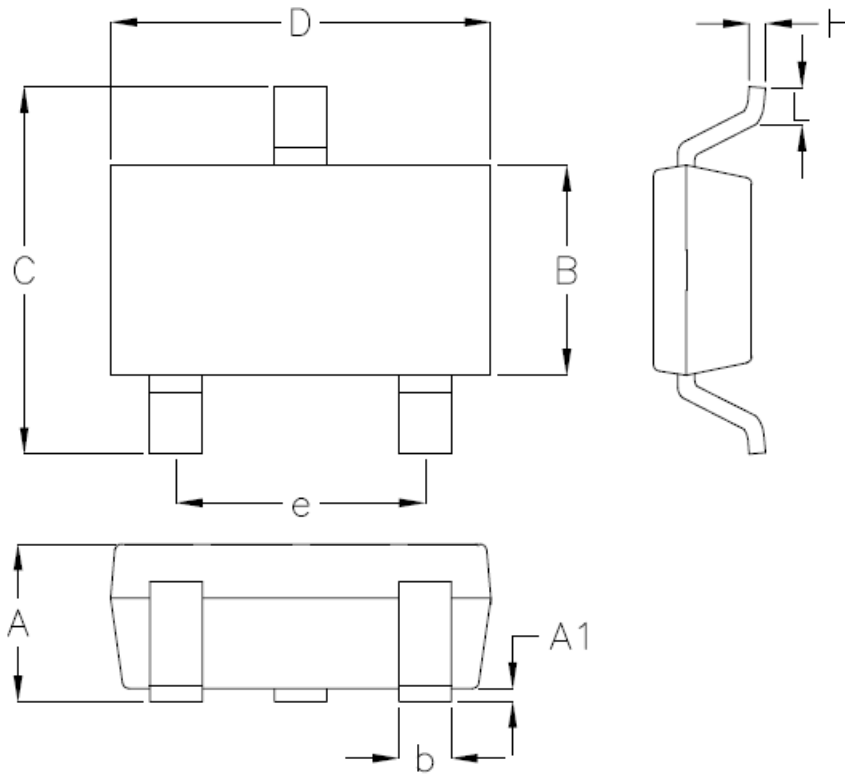
**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**

# JHT3107

## SOT-23S Package Outline



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.890	1.295	0.035	0.051
A1	0.000	0.152	0.000	0.006
B	1.200	1.400	0.047	0.055
b	0.300	0.508	0.012	0.020
C	2.100	2.640	0.083	0.104
D	2.692	3.099	0.106	0.122
e	1.793	2.007	0.070	0.079
H	0.080	0.254	0.003	0.010
L	0.300	0.610	0.012	0.024

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